IN THE CLAIMS:

1. (Currently Amended) A chip-type semiconductor light-emitting device, comprising:

a pair of electrodes, at least one of said pair of electrodes including an inner portion and an outer portion, the inner portion of the at least one of said pair of electrodes residing in the same plane as the outer portion of the at least one of said pair of electrodes;

a semiconductor light-emitting chip electrically connected to said pair of electrodes;

a mold encapsulating said semiconductor light-emitting chip, said mold encapsulating said inner portion of at least one of said pair of electrodes, said outer portion of at least one of said pair of electrodes extending substantially laterally beyond said mold; and

a step formed by only a metal layer in said inner portion of at least one of said pair of electrodes at an inside of said mold, said step having a height increasing from an outer side to an inner side of said mold.

2. (Previously Amended) A chip-type semiconductor light-emitting device according to claim 1, wherein said electrode includes a Cu layer, said step being formed by changing a thickness of said Cu layer.

3. (Previously Amended) A chip-type semiconductor light-emitting device according to claim 1, wherein said electrode includes an Au layer formed in an uppermost layer thereof.

4. (Previously Added) A chip-type semiconductor light-emitting device according to claim 2, wherein said electrode includes an Au layer formed in an uppermost layer thereof.